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I hereby certify that this correspondence is being deposited via express mail certificate number EU792488348US with the United States Postal Service addressed to: missioner of Patents and Trademarks, Alexandria, VA on May24, 2005. The applicant and/or attorney requests the end of deposit as the filing date. Depositor: N1cole Ba

Michel Barre 5/24/05 (Signature & date)

JC06 Rec'd PCT/PTO 24 MAY 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

May 24, 2005

Doris, et al. :

Group Art Unit: To be assigned

Serial No: To be assigned :

Examiner:

Filed: 11/25/02

International Business Machines Corporation

2070 Route 52

Hopewell Junction, NY 12533

TITLE: Strained FINFET CMOS Device Structures

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the US and non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or nonpertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,

Doris, et al.

Joseph P. Abate

Registration No. 30,238 Telephone No. 845,894-4633

JC06 Rec'd PCT/PTO 2.4 MAY 2005



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		US 2001/0009784 A1	7-26-01	Ma, et al.				
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		Devices, vol. 41, no. 4, A	pril 1994, pp. 53	ed npn-112 33-38.	ansistors- Mechanisms and	l MoGenng.∵ 1	EEE Transacu	OBS OB LIC	ectron
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Docket Number (Optional) FIS920020105



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				J.S. PATENT	DOCUMENTS					
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		6,501,121	12-31-02	Yu, et a	Yu, et al.					
		6,506,652	1-14-03	Jan, et a	Jan, et al. Jan, et al.					
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Applicant(s)

Doris, et al.

Group Art Unit

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		6,342,410	1-29-02	Yu					KOTKIATE
		6,413,802	7-2-02	Hu, et al					
		6,433,609	8-13-02	Voldman					
		6,458,662	10-1-02	Yu					
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